## NSN 5961-01-175-8750

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-175-8750 **Inclosure Material:** Ceramic and metal **Overall Length:** 1.646 inches **Mounting Facility Quantity: Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Threaded stud **Overall Width Across Flats:** Between 0.544 inches and 0.563 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 10.0 gate voltage, dc **Current Rating Per Characteristic:** 40.00 amperes forward current, average of standard range and 175.00 amperes forward current, average preset **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius case **Test Data Document:** 18876-me43900200001 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 2 tab, solder lug and 1 threaded stud Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: